

Medium power transistor ($-32V$, $-2A$)

2SB1182 / 2SB1240

●Features

- 1) LOW $V_{CE(sat)}$.

$$V_{CE(sat)} = -0.5V \text{ (Typ.)}$$

$$(I_C/I_B = -2A / -0.2A)$$

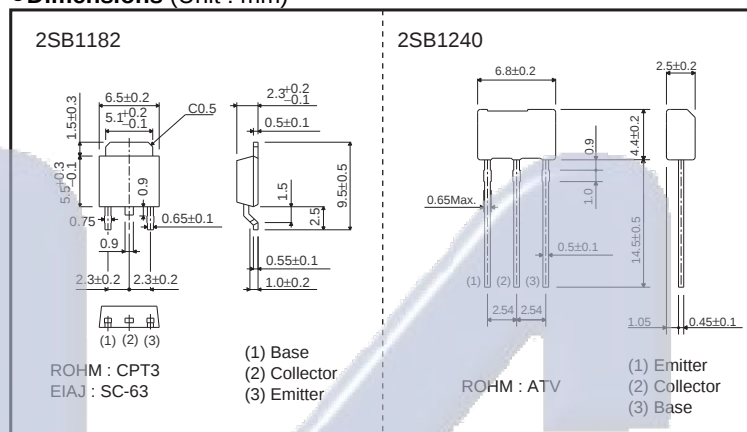
- 2) Complements 2SD1758 / 2SD1862.

●Structure

Epitaxial planar type

Epitaxial planar type
PNP silicon transistor

●Dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CB0}	-40	V
Collector-emitter voltage		V_{CE0}	-32	V
Emitter-base voltage		V_{EB0}	-5	V
Collector current		I_c	-2	A(DC)
			-3	A (Pulse) *1
Collector power dissipation	2SB1182	P_c	10	W ($T_c=25^{\circ}\text{C}$)
	2SB1240		1	W *2
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature		T_{stg}	-55 to 150	$^{\circ}\text{C}$

*1 Single pulse, Pw=100ms

*2 Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-40	-	-	V	$I_{C=-50\mu A}$
Collector-emitter breakdown voltage	BV_{CEO}	-32	-	-	V	$I_{C=-1mA}$
Emitter-base breakdown voltage	BV_{EBO}	-5	-	-	V	$I_{E=-50\mu A}$
Collector cutoff current	I_{CBO}	-	-	-1	μA	$V_{CB=-20V}$
Emitter cutoff current	I_{EBO}	-	-	-1	μA	$V_{EB=-4V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-0.5	-0.8	V	$I_C/I_B=-2A/-0.2A$ *
DC current transfer ratio	h_{FE}	120	-	390	-	$V_{CE=-3V}, I_{C=-0.5A}$ *
Transition frequency	f_T	-	100	-	MHz	$V_{CE=-5V}, I_E=0.5A, f=100MHz$
Output capacitance	C_{ob}	-	50	-	pF	$V_{CB=-10V}, I_E=0A, f=1MHz$

* Measured using pulse current.

●Packaging specifications and h_{FE}

Type	h_{FE}	Package	Taping	
		Code	TL	TV2
		Basic ordering unit (pieces)	2500	2500
2SB1182	QR		○	—
2SB1240	QR		—	○

h_{FE} values are classified as follows :

Item	Q	R
h_{FE}	120 to 270	180 to 390

●Electrical characteristic curves

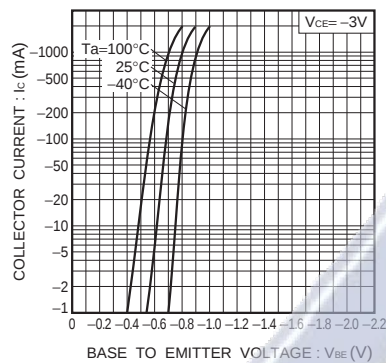


Fig.1 Grounded emitter propagation characteristics

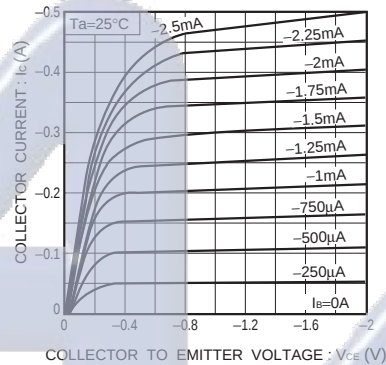


Fig.2 Grounded emitter output characteristics

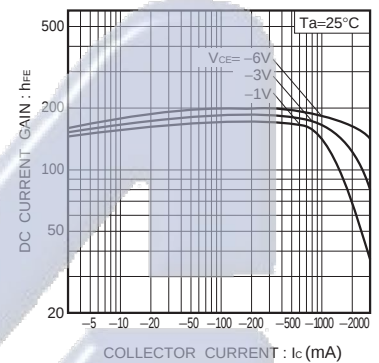


Fig.3 DC current gain vs. collector current (I)

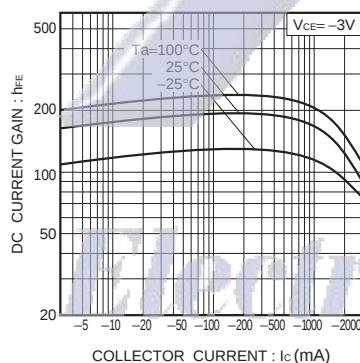


Fig.4 DC current gain vs. collector current (II)

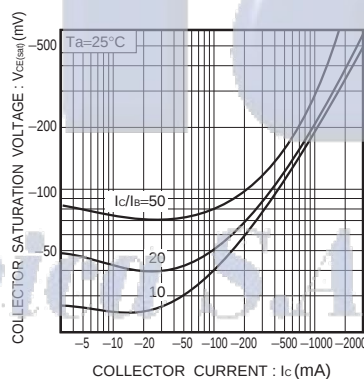


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

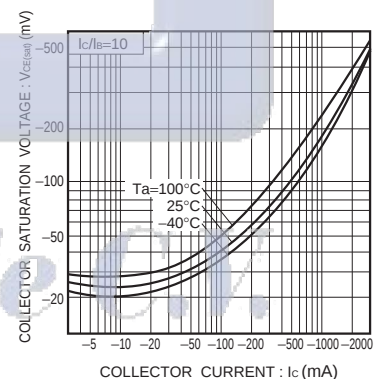


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

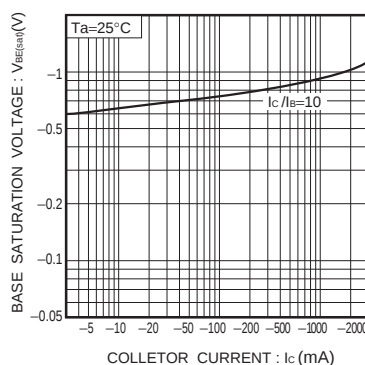


Fig.7 Base-emitter saturation voltage vs. collector current

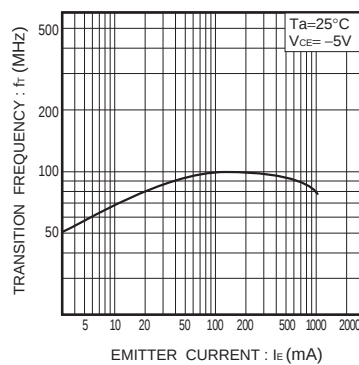
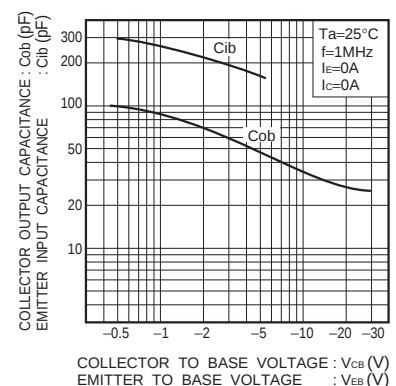


Fig.8 Gain bandwidth product vs. emitter current

Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

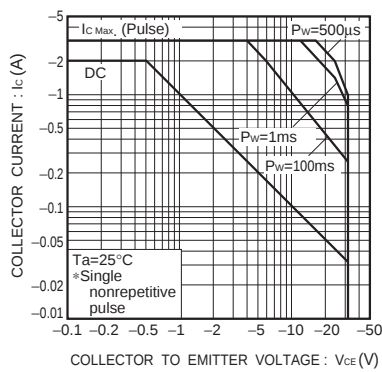


Fig.10 Safe operation area
(2SB1182)

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